

## **Small Signal Product**

# 300mW, NPN Small Signal Transistor

#### **FEATURES**

- Epitaxial planar die construction
- Surface device type mounting
- Moisture sensitivity level 1
- Matte Tin (Sn) lead finish with Nickel (Ni) underplate
- Pb free version and RoHS compliant
- Packing code with suffix "G" means green compound (halogen-free)

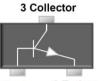
### MECHANICAL DATA

- Case: SOT- 23, molded plastic
- Terminal: Matte tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- High temperature soldering guaranteed: 260°C/10s
- Weight: 8 mg (approximately)
- Marking Code: 1E.





1 Base 2 Emitter







MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T <sub>A</sub> =25°C unless otherwise noted)				
PARAMETER	SYMBOL	VALUE	UNIT	
Power Dissipation	P <sub>D</sub>	300	mW	
Collector-Base Voltage	$V_{CBO}$	60	V	
Collector-Emitter Voltage	$V_{CEO}$	40	V	
Emitter-Base Voltage	$V_{EBO}$	6	V	
Collector Current	I <sub>C</sub>	200	mA	
Junction and Storage Temperature Range	$T_J,T_STG$	-55 to +150	°C	

Notes: Valid provided that electrodes are kept at ambient temperature

PARAMETER			SYMBOL	MIN	MAX	UNIT	
Collector-Base Breakdov	vn Voltage	I <sub>C</sub> = 10 μA	I <sub>E</sub> = 0	$V_{(BR)CBO}$	60	-	V
Collector-Emitter Breakd	own Voltage	I <sub>C</sub> = 1 mA	I <sub>B</sub> = 0	$V_{(BR)CEO}$	40	-	V
Emitter-Base Breakdowr	ı Voltage	I <sub>E</sub> = 10 μA	I <sub>C</sub> = 0	$V_{(BR)EBO}$	6	-	V
Collector Cut-off Current		V <sub>CB</sub> = 60 V	I <sub>E</sub> = 0	I <sub>CBO</sub>	-	0.1	μA
Collector Cut-off Current		V <sub>CE</sub> = 30 V	$V_{BE(OFF)} = 3 V$	I <sub>CEO</sub>	-	50	nA
Emitter Cut-off Current		V <sub>EB</sub> = 5 V	I <sub>C</sub> = 0	I <sub>EBO</sub>	-	0.1	μA
		V <sub>CE</sub> = 1 V	I <sub>C</sub> = 10 mA		100	400	
DC Current Gain		$V_{CE} = 1 V$	$I_C = 50 \text{ mA}$	h <sub>FE</sub>	60	-	
		$V_{CE} = 1 V$	$I_C = 100 \text{ mA}$		30	-	
Collector-Emitter Saturation Voltage		$I_C = 50 \text{ mA}$	I <sub>B</sub> = 5 mA	V <sub>CE(sat)</sub>	-	0.3	V
Base-Emitter Saturation	Voltage	$I_C = 50 \text{ mA}$	I <sub>B</sub> = 5 mA	V <sub>BE(sat)</sub>	-	0.95	V
Transition frequency	V <sub>CE</sub> = 20 V	I <sub>C</sub> = 10 mA	f= 100MHz	f <sub>T</sub>	250	-	MHz
Delay time	V <sub>CC</sub> = 3 V	V <sub>BE</sub> = 0.5 V	I <sub>C</sub> = 10 mA	t <sub>d</sub>	-	35	ns
Rise time			$I_{B1} = 1.0 \text{ mA}$	t <sub>r</sub>	-	35	ns
Storage time		V <sub>CC</sub> = 3 V	I <sub>C</sub> = 10 mA	t <sub>s</sub>	-	200	ns
Fall time		$I_{B1} = I_{B2} = 1.0$	mA	t <sub>f</sub>	-	50	ns

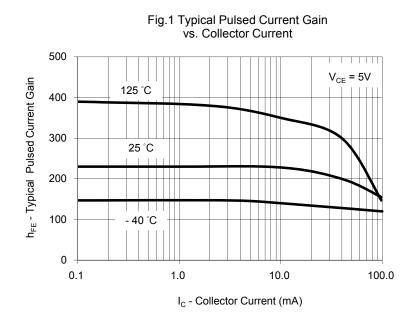
- 40 °C



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#### RATINGS AND CHARACTERISTICS CURVES

(T<sub>A</sub>=25°C unless otherwise noted)



vs. Collector Current  $\beta = 10$   $125 ^{\circ}C$   $25 ^{\circ}C$ 

Fig. 2 Collector-Emitter Saturation Voltage

0.20

0.15

0.10

0.05

0.00

V <sub>CESAT</sub>- Collector-Emitter Voltage (V)

I<sub>C</sub> - Collector Current (mA)

Fig. 3 Base-Emitter Saturation Voltage vs. Collector Current

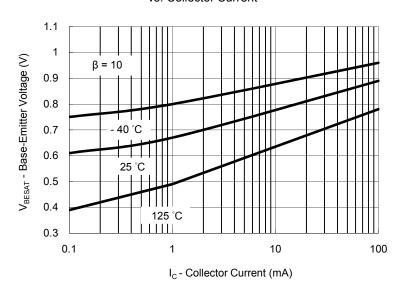


Fig. 4 Base-Emitter On Voltage vs. Collector Current

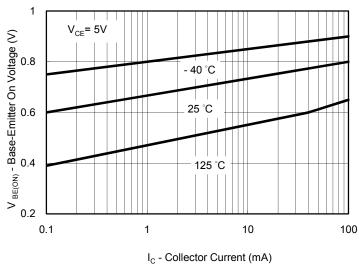


Fig. 5 Collector-Cutoff Current vs. Ambient Temperature

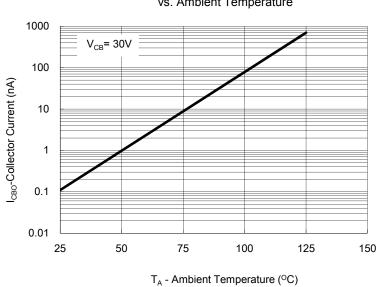
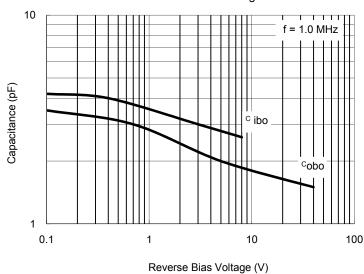


Fig. 6 Capacitance vs. Reverse Bias Voltage

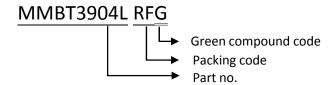


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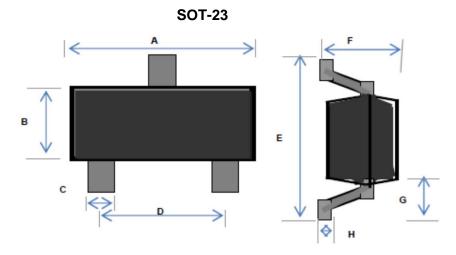


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# ORDER INFORMATION (EXAMPLE)

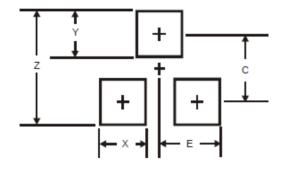


### PACKAGE OUTLINE DIMENSIONS



DIM.	Unit(mm)		Unit(inch)	
DIN.	Min	Max	Min	Max
Α	2.70	3.10	0.106	0.122
В	1.10	1.50	0.043	0.059
С	0.30	0.51	0.012	0.020
D	1.78	2.04	0.070	0.080
Е	2.10	2.64	0.083	0.104
F	0.89	1.30	0.035	0.051
G	0.55	REF	0.022	REF
Н	0.10	REF	0.004	REF

### SUGGEST PAD LAYOUT



DIM	Unit (mm)	Unit (inch)	
DIIVI	TYP	TYP	
Z	2.90	0.114	
Χ	0.80	0.031	
Υ	0.90	0.035	
С	2.00	0.079	
F	1.35	0.053	







# **Small Signal Product**

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